

## IN THE CLAIMS:

1. (original) A MOSFET gate structure comprising:  
a gate dielectric overlying a substrate;  
a predominantly niobium monoxide gate overlying  
the gate dielectric.
2. (original) The gate structure of claim 1, wherein  
the predominantly niobium monoxide gate has a work function  
between approximately 4.1 eV and 4.4 eV.
3. (original) The gate structure of claim 1, wherein  
the gate dielectric is silicon dioxide.
4. (original) The gate structure of claim 1, wherein  
the gate dielectric comprises a high-k gate dielectric material.
5. (original) The gate structure of claim 4, wherein  
the high-k gate dielectric material comprises HfO<sub>2</sub>, ZrO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>,  
Ta<sub>2</sub>O<sub>5</sub>, HfAlO or HfSiO<sub>4</sub>.
6. (original) The gate structure of claim 1, further  
comprising a capping layer overlying the niobium monoxide  
gate.
7. (original) The gate structure of claim 6, wherein  
the capping layer is silicon nitride.

8. (original) The gate structure of claim 6, wherein the capping layer is a conductive barrier metal.

9. (original) The method of claim 8, wherein the conductive barrier metal is TiN.

10. (original) A MOSFET gate structure comprising:  
a high-k gate dielectric overlying a substrate;  
a conductive metal-monoxide layer having a work  
function of between approximately 4.1 eV and 4.4 eV  
overlying the gate dielectric.

11. (original) The MOSFET gate structure of claim  
10, wherein the conductive metal-monoxide comprises niobium  
oxide.